



April 1995

HGTP20N35G3VL, HGT1S20N35G3VL, HGT1S20N35G3VLS

20A, 350V N-Channel, Logic Level, Voltage Clamping IGBTs

Features

- Logic Level Gate Drive
- Internal Voltage Clamp
- ESD Gate Protection
- $T_J = 175^{\circ}\text{C}$
- Ignition Energy Capable

Description

This N-Channel IGBT is a MOS gated, logic level device which is intended to be used as an ignition coil driver in automotive ignition circuits. Unique features include an active voltage clamp between the collector and the gate which provides Self Clamped Inductive Switching (SCIS) capability in ignition circuits. Internal diodes provide ESD protection for the logic level gate. Both a series resistor and a shunt resistor are provided in the gate circuit.

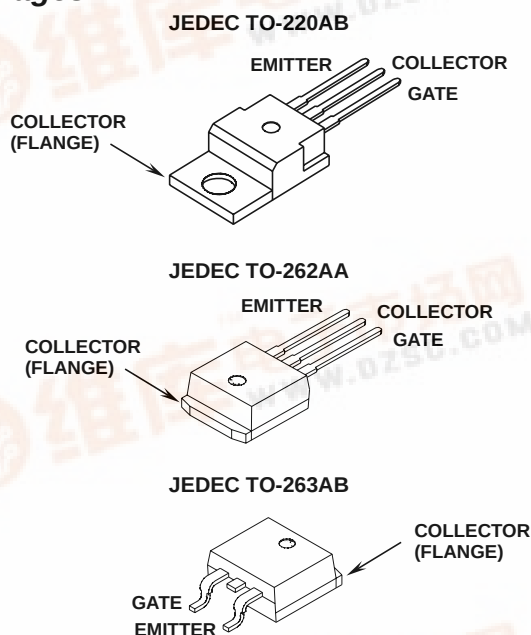
PACKAGING AVAILABILITY

PART NUMBER	PACKAGE	BRAND
HGTP20N35G3VL	T0-220AB	20N35GVL
HGT1S20N35G3VL	T0-262AA	20N35GVL
HGT1S20N35G3VLS	T0-263AB	20N35GVL

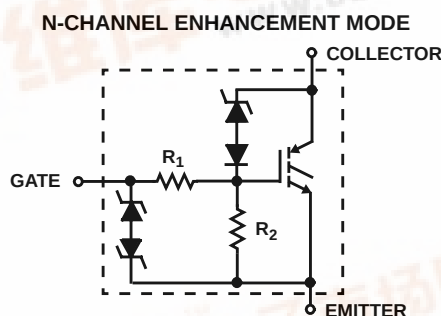
NOTE: When ordering, use the entire part number. Add the suffix 9A to obtain the T0-263AB variant in the tape and reel, i.e., HGT1S20N35G3VLS9A.

The development type number for this device is TA49076.

Packages



Terminal Diagram



Absolute Maximum Ratings $T_C = +25^{\circ}\text{C}$, Unless Otherwise Specified

Collector-Emitter Bkdn Voltage At 10mA, $R_{GE} = 1\text{k}\Omega$	BV_{CER}
Emitter-Collector Bkdn Voltage At 10mA	BV_{ECS}
Collector Current Continuous At $V_{GE} = 5.0\text{V}$, $T_C = +25^{\circ}\text{C}$, Figure 7	I_{C25}
At $V_{GE} = 5.0\text{V}$, $T_C = +100^{\circ}\text{C}$	I_{C100}
Gate-Emitter-Voltage (Note)	V_{GES}
Inductive Switching Current At $L = 2.3\text{mH}$, $T_C = +25^{\circ}\text{C}$	I_{SCIS}
At $L = 2.3\text{mH}$, $T_C = +175^{\circ}\text{C}$	I_{SCIS}
Collector to Emitter Avalanche Energy At $L = 2.3\text{mH}$, $T_C = +25^{\circ}\text{C}$	E_{AS}
Power Dissipation Total At $T_C = +25^{\circ}\text{C}$	P_D
Power Dissipation Derating $T_C > +25^{\circ}\text{C}$	
Operating and Storage Junction Temperature Range	T_J, T_{STG}
Maximum Lead Temperature for Soldering	T_L
Electrostatic Voltage at 100pF, 1500 Ω	ESD

NOTE: May be exceeded if I_{GEM} is limited to 10mA.

		UNITS
HGTP20N35G3VL		
HGT1S20N35G3VL		
HGT1S20N35G3VLS		
	375	V
	24	V
	20	A
	20	A
	± 10	V
	26	A
	18	A
	775	mJ
	150	W
	1.0	W/ $^{\circ}\text{C}$
	-40 to +175	$^{\circ}\text{C}$
	260	$^{\circ}\text{C}$
	6	KV

Specifications HGTP20N35G3VL, HGT1S20N35G3VL, HGT1S20N35G3VLS

Electrical Specifications $T_C = +25^{\circ}\text{C}$, Unless Otherwise Specified

PARAMETERS	SYMBOL	TEST CONDITIONS		LIMITS			UNITS
				MIN	TYP	MAX	
Collector-Emitter Breakdown Voltage	BV_{CES}	$I_C = 10\text{mA}$, $V_{GE} = 0\text{V}$	$T_C = +175^{\circ}\text{C}$	310	345	380	V
			$T_C = +25^{\circ}\text{C}$	320	350	380	V
			$T_C = -40^{\circ}\text{C}$	320	355	390	V
Collector-Emitter Breakdown Voltage	BV_{CER}	$I_C = 10\text{mA}$ $V_{GE} = 0\text{V}$ $R_{GE} = 1\text{k}\Omega$	$T_C = +175^{\circ}\text{C}$	300	340	375	V
			$T_C = +25^{\circ}\text{C}$	315	345	375	V
			$T_C = -40^{\circ}\text{C}$	315	350	390	V
Gate-Emitter Plateau Voltage	V_{GEP}	$I_C = 10\text{A}$ $V_{CE} = 12\text{V}$	$T_C = +25^{\circ}\text{C}$	-	3.7	-	V
Gate Charge	$Q_{G(ON)}$	$I_C = 10\text{A}$ $V_{GE} = 5\text{V}$ $V_{CE} = 12\text{V}$	$T_C = +25^{\circ}\text{C}$	-	28.7	-	nC
Collector-Emitter Clamp Bkdn. Voltage	$BV_{CE(CL)}$	$I_C = 10\text{A}$ $R_G = 0\Omega$	$T_C = +175^{\circ}\text{C}$	325	360	395	V
Emitter-Collector Breakdown Voltage	BV_{ECS}	$I_C = 10\text{mA}$	$T_C = +25^{\circ}\text{C}$	20	32	-	V
Collector-Emitter Leakage Current	I_{CES}	$V_{CE} = 250\text{V}$	$T_C = +25^{\circ}\text{C}$	-	-	5	μA
		$V_{CE} = 250\text{V}$	$T_C = +175^{\circ}\text{C}$	-	-	250	μA
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = 10\text{A}$ $V_{GE} = 4.5\text{V}$	$T_C = +25^{\circ}\text{C}$	-	1.3	1.6	V
			$T_C = +175^{\circ}\text{C}$	-	1.25	1.5	V
		$I_C = 20\text{A}$ $V_{GE} = 5.0\text{V}$	$T_C = +25^{\circ}\text{C}$	-	1.6	2.8	V
			$T_C = +175^{\circ}\text{C}$	-	1.9	3.5	V
Gate-Emitter Threshold Voltage	$V_{GE(TH)}$	$I_C = 1\text{mA}$ $V_{CE} = V_{GE}$	$T_C = +25^{\circ}\text{C}$	1.3	1.8	2.3	V
Gate Series Resistance	R_1		$T_C = +25^{\circ}\text{C}$	-	1.0	-	$\text{k}\Omega$
Gate-Emitter Resistance	R_2		$T_C = +25^{\circ}\text{C}$	10	17	25	$\text{k}\Omega$
Gate-Emitter Leakage Current	I_{GES}	$V_{GE} = \pm 10\text{V}$		± 400	± 590	± 1000	μA
Gate-Emitter Breakdown Voltage	BV_{GES}	$I_{GES} = \pm 2\text{mA}$		± 12	± 14	-	V
Current Turn-Off Time-Inductive Load	$t_{D(OFF)I} + t_{F(OFF)I}$	$I_C = 10\text{A}$, $R_G = 25\Omega$, $L = 550\text{H}$, $R_L = 26.4\Omega$, $V_{GE} = 5\text{V}$, $V_{CL} = 300\text{V}$, $T_C = +175^{\circ}\text{C}$		-	15	30	μs
Inductive Use Test	I_{SCIS}	$L = 2.3\text{mH}$, $V_G = 5\text{V}$, $R_G = 0\Omega$	$T_C = +175^{\circ}\text{C}$	18	-	-	A
			$T_C = +25^{\circ}\text{C}$	26	-	-	A
Thermal Resistance	$R_{\theta JC}$			-	-	1.0	$^{\circ}\text{C/W}$

HGTP20N35G3VL, HGT1S20N35G3VL, HGT1S20N35G3VLS

Typical Performance Curves

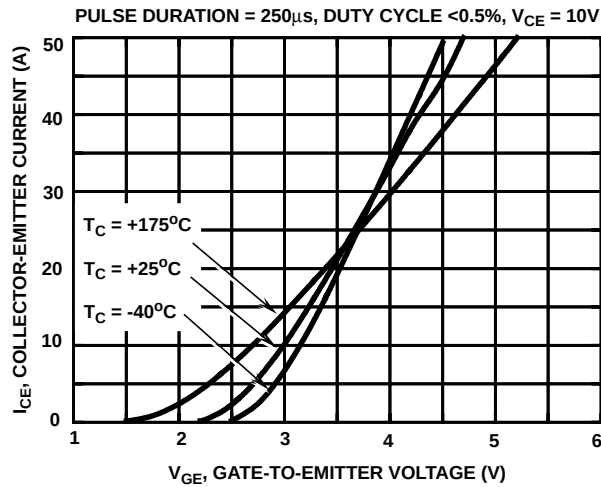


FIGURE 1. TRANSFER CHARACTERISTICS

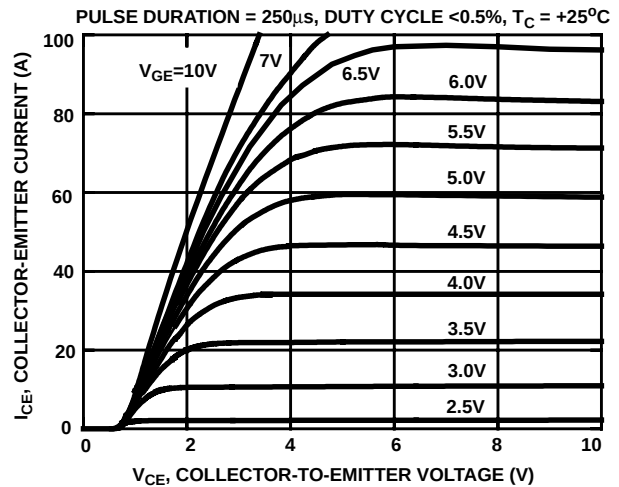


FIGURE 2. SATURATION CHARACTERISTICS

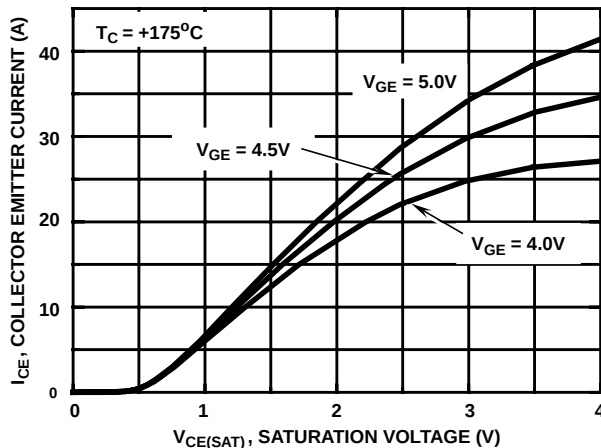


FIGURE 3. COLLECTOR-EMITTER CURRENT AS A FUNCTION OF SATURATION VOLTAGE

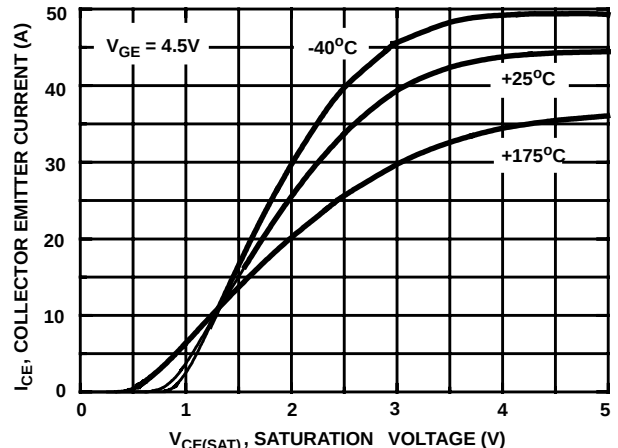


FIGURE 4. COLLECTOR-EMITTER CURRENT AS A FUNCTION OF SATURATION VOLTAGE

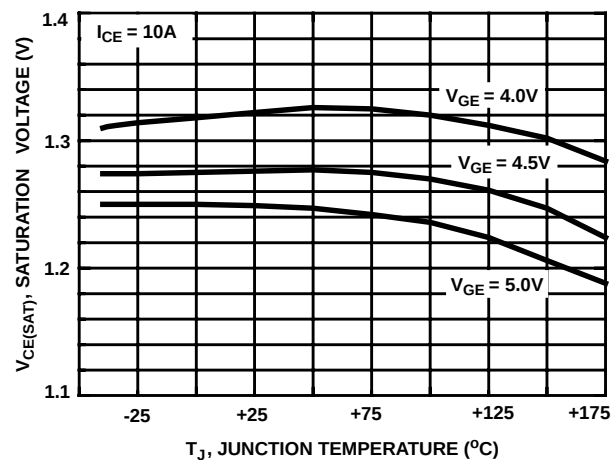


FIGURE 5. SATURATION VOLTAGE AS A FUNCTION OF JUNCTION TEMPERATURE

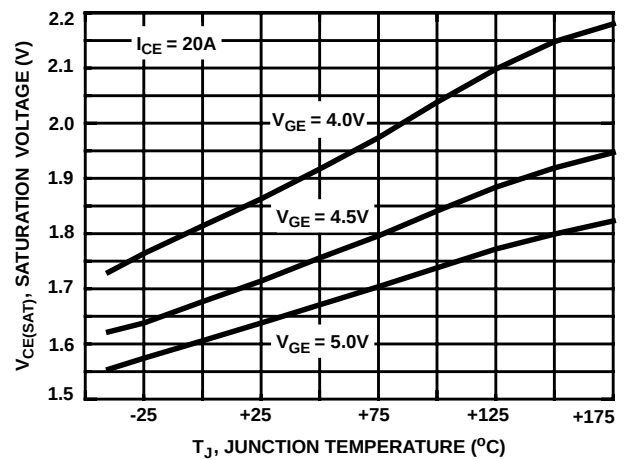


FIGURE 6. SATURATION VOLTAGE AS A FUNCTION OF JUNCTION TEMPERATURE

HGTP20N35G3VL, HGT1S20N35G3VL, HGT1S20N35G3VLS

Typical Performance Curves (Continued)

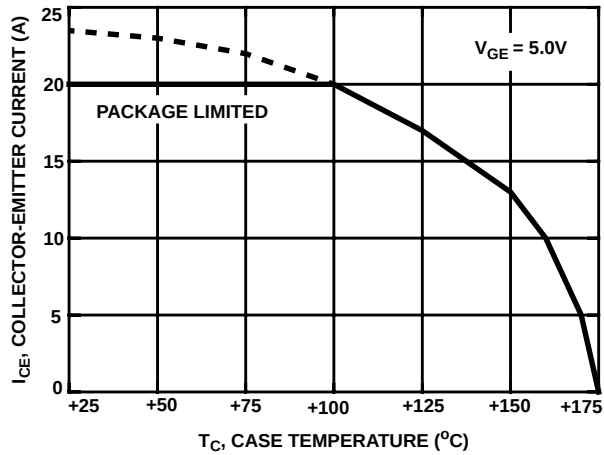


FIGURE 7. COLLECTOR-EMITTER CURRENT AS A FUNCTION OF CASE TEMPERATURE

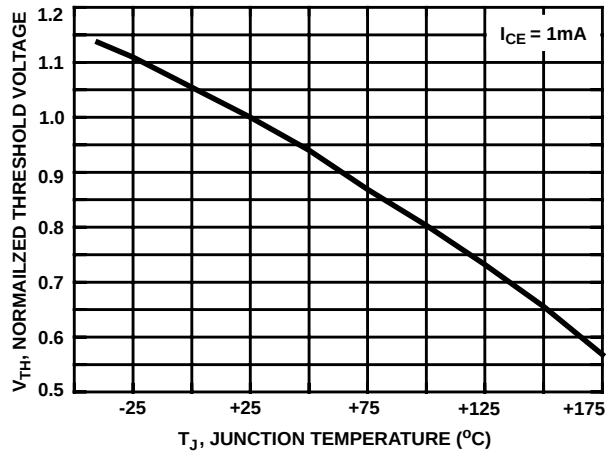


FIGURE 8. NORMALIZED THRESHOLD VOLTAGE AS A FUNCTION OF JUNCTION TEMPERATURE

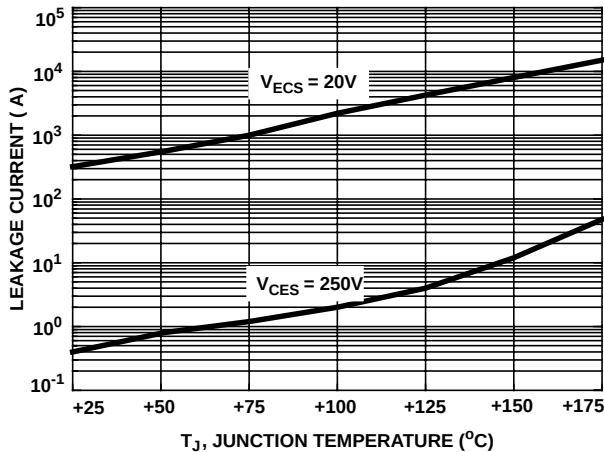


FIGURE 9. LEAKAGE CURRENT AS A FUNCTION OF JUNCTION TEMPERATURE

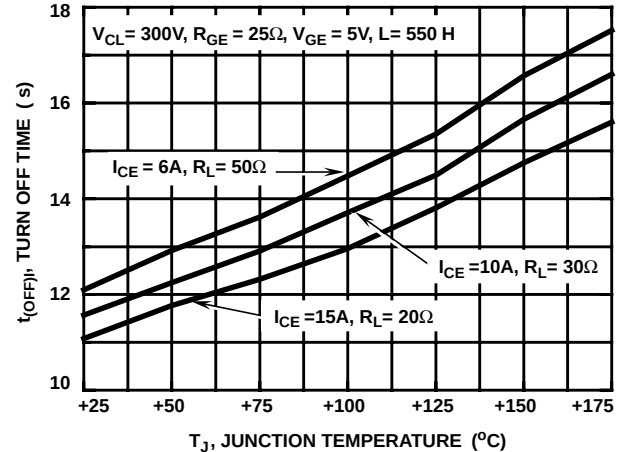


FIGURE 10. TURN-OFF TIME AS A FUNCTION OF JUNCTION TEMPERATURE

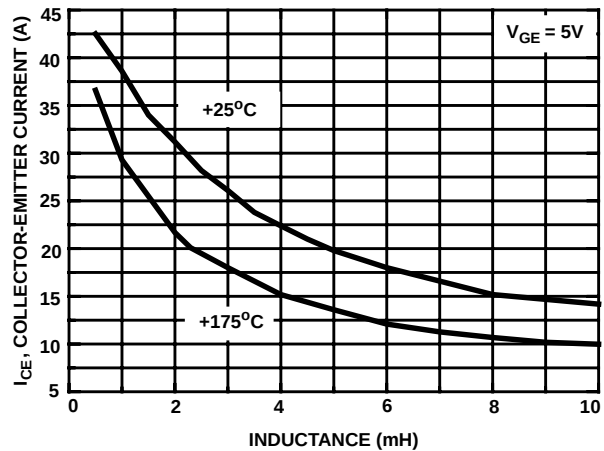


FIGURE 11. SELF CLAMPED INDUCTIVELY SWITCHING CURRENT AS A FUNCTION OF INDUCTANCE

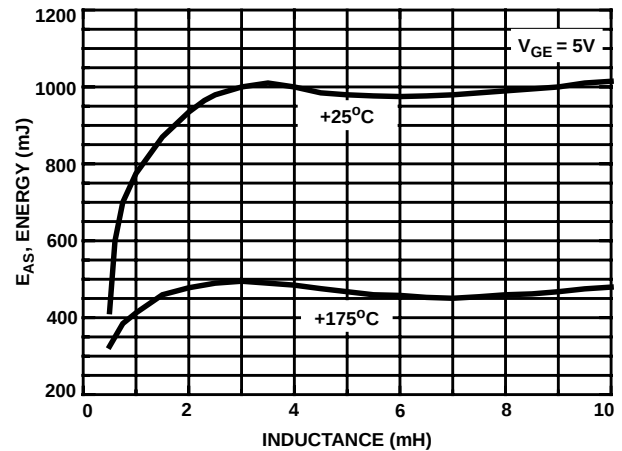


FIGURE 12. SELF CLAMPED INDUCTIVELY SWITCHING ENERGY AS A FUNCTION OF INDUCTANCE

HGTP20N35G3VL, HGT1S20N35G3VL, HGT1S20N35G3VLS

Typical Performance Curves (Continued)

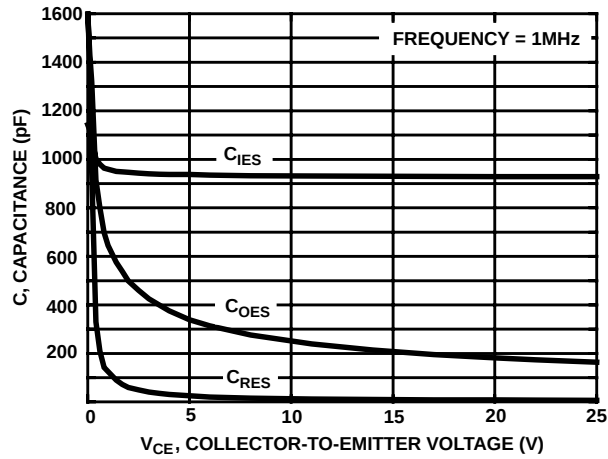


FIGURE 13. CAPACITANCE AS A FUNCTION OF COLLECTOR-EMITTER VOLTAGE

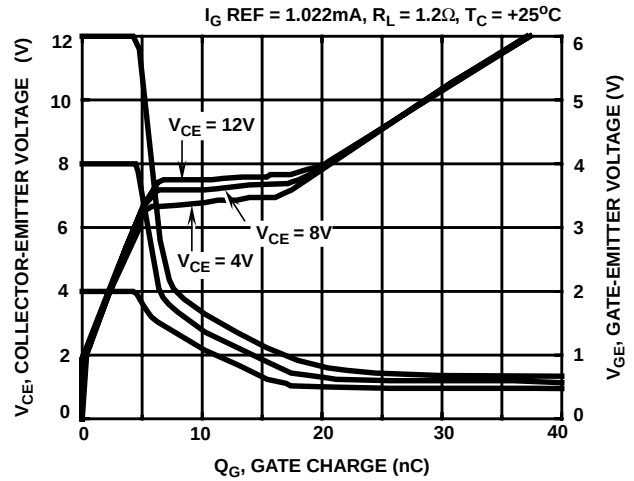


FIGURE 14. GATE CHARGE WAVEFORMS

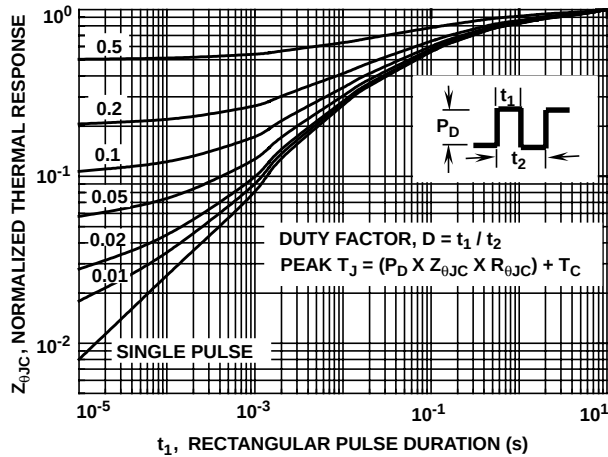


FIGURE 15. NORMALIZED TRANSIENT THERMAL IMPEDANCE, JUNCTION TO CASE

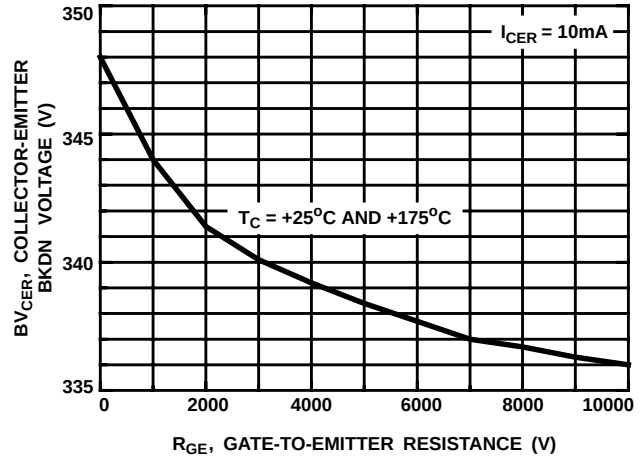


FIGURE 16. BREAKDOWN VOLTAGE AS A FUNCTION OF GATE - Emitter RESISTANCE

Test Circuits

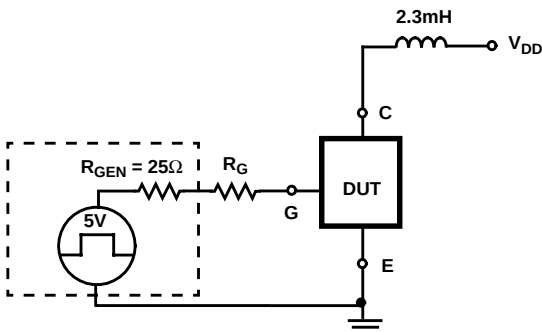


FIGURE 17. USE TEST CIRCUIT

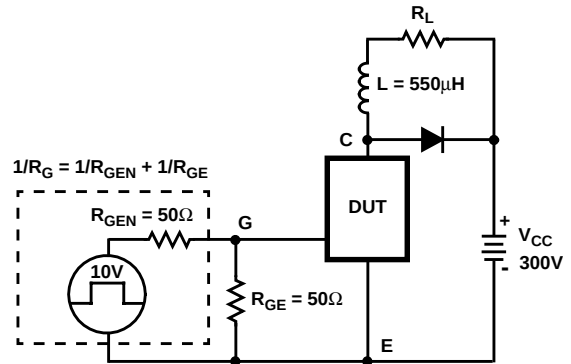


FIGURE 18. INDUCTIVE SWITCHING TEST CIRCUIT

HGTP20N35G3VL, HGT1S20N35G3VL, HGT1S20N35G3VLS

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